Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	92	(MRAM ((magnetic ferromagnetic) near memory) TMR GMR ferromagnetic) near insulat$3 near (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:27
L2	6	1 and (((connect$3 contact) near hole) plug)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:16
L3	3	1 and ((connect$3 contact) near hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:28
L4	13603	(MRAM ((magnetic ferromagnetic) near memory) TMR GMR ferromagnetic) and ((insulat$3 oxide) near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:27
L5	950	4 and ((connect$3 contact) near hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:28
L6	230	5 and plug	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:28
L7	161	6 and (BL (bit adj line))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/10 09:28